

Attorney Docket No. 5308-27




PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Sei-Hyung Ryu
Serial No.: 10/698,170
Filed: October 30, 2003

Confirmation No. 2502
Group Art Unit: 2811
Examiner: Tran, Long K.

For: **VERTICAL JFET LIMITED SILICON CARBIDE POWER METAL-OXIDE
SEMICONDUCTOR FIELD EFFECT TRANSISTORS AND METHODS OF
FABRICATING VERTICAL JFET SILICON CARBIDE METAL-OXIDE
SEMICONDUCTOR FIELD EFFECT TRANSISTORS**

Date: April 26, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

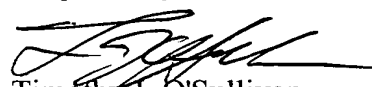
INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. Copies of the listed U.S. patents and U.S. patent application publications are not provided herewith in accordance with the amendment by the U.S. Patent and Trademark Office to 37 C.F.R. § 1.98(a)(2)(ii) effective October 21, 2004.

It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP. No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,


Timothy J. O'Sullivan
Registration No. 35,632

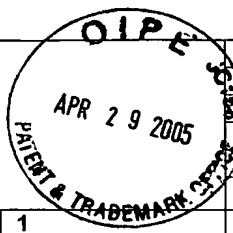
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Erin A. Campion

Substitute form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/698,170
		Filing Date	October 30, 2003
		First Named Inventor	Sei-Hyung Ryu
		Group Art Unit	2811
		Examiner Name	Tran, Long K.
Sheet 1 of 1	Attorney Docket Number	5308-279	



U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
	1	6,303,508	B1	Alok	10/2001
	2	6,297,100	B1	Kumar et al.	10/2001
	3	6,133,587		Takeuchi et al.	10/2000
	4	6,025,233		Teresawa	02/2000
	5	6,020,600		Miyajima et al.	02/2000
	6	5,976,936		Miyajima et al.	11/1999
	7	5,917,203		Bhatnagar et al.	06/1999
	8	5,877,041		Fuller	03/1999
	9	5,851,908		Harris et al.	12/1998
	10	5,837,572		Gardner et al.	11/1998
	11	5,814,859		Ghezze et al.	9/29/98
	12	5,804,483		Harris	09/1998
	13	5,734,180		Malhi	03/1998
	14	5,710,059		Rottner	01/1998
	15	5,510,281		Ghezze et al.	4/23/96
	16	5,393,999		Malhi	02/1995
	17	5,384,270		Ueno	01/1995
	18	5,348,895		Smayling et al.	09/1994
	19	3,629,011		Tohi et al.	12/1971

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Office	Number	Kind Code (if known)		
	20	WO	97/08754			03/1997

OTHER NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published		
	21	Palmour et al. "SiC Device Technology: Remaining Issues," Diamond and Related Materials. vol. 6, 1997, pp. 1400-1404.		
	22	Rao et al. "P-N Junction Formation in 6H-SiC by Acceptor Implantation into N-Type Substrate," Nuclear Instruments and Methods in Physics Research B. vol. 106, 1995, pp. 333-338.		
	23	Rao et al. "Al and N Ion Implantations in 6H-SiC," Silicon Carbide and Related Materials. 1995 Conf, Kyoto, Japan. Published 1996.		
	24	Capano, M.A., et al., Ionization Energies and Electron Mobilities in Phosphorus--and Nitrogen-Implanted 4H-Silicon Carbide, IEEE ICSCRM Conference 1999, Research Triangle Park, North Carolina (Oct. 10-13, 1999).		
	25	Patel, R., et al., Phosphorus-Implanted High-Voltage N.sup.+ P 4H-SiC Junction Rectifiers, Proceedings of 1998 International Symposium on Poer Semiconductor Devices & ICs, pp. 387-390 (Kyoto).		
	26	Dastidar, Sujoyita, A Study of P-Type Activation in Silicon Carbide, Thesis (Purdue University, May 1998).		

Examiner Signature	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.